

## WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:  
an insulating layer;  
5 an interconnect line embedded in said insulating layer;  
a circuit element mounted on said insulating layer;  
a packaging layer formed to cover said circuit element;  
and  
an electroconductive shielding film formed to cover said  
10 packaging layer,  
wherein said interconnect line is electrically coupled  
to said shielding film.
2. The semiconductor device according to claim 1, further  
15 comprising a protective film formed to cover said shielding film,  
said protective film comprising a material having higher  
corrosion resistance than that of a material that is included  
in said shielding film.
- 20 3. A method for manufacturing a semiconductor device having  
a circuit element by dividing a multi-layer member, said  
multi-layer member comprising an insulating layer; an  
interconnect line embedded in said insulating layer; said  
circuit element mounted on a surface of said insulating layer;  
25 and a packaging layer formed to cover said circuit element,  
comprising:  
forming a dividing gutter on a surface of said multi-layer  
member to create an exposed side surface of said interconnect  
line;  
30 covering the front surface of said multi-layer member  
with an electroconductive material to form a shielding film,  
said shielding film being electrically coupled to said  
interconnect line; and

cutting said multi-layer member off from the backside thereof along said dividing gutter to separate said circuit element of the multi-layer member from the rest regions thereof.

5     4.     The method according to claim 3, further comprising:  
            grounding said interconnect line.

            5.     The method according to claim 3 , further comprising:  
                    wherein a plurality of the circuit elements are mounted  
10    on said insulating layer, and said interconnect line is provided  
            to be coupled to said plurality of the circuit elements before  
            forming said dividing gutter, and

                    wherein said dividing gutter includes dividing said  
            interconnect line so that each of the divided interconnect lines  
15    is coupled to each of said circuit elements, respectively.

            6.     The method according to claim 4, further comprising:  
                    wherein a plurality of the circuit elements are mounted  
            on said insulating layer, and said interconnect line is provided  
20    to be coupled to said plurality of the circuit elements before  
            forming said dividing gutter, and

                    wherein said dividing gutter includes dividing said  
            interconnect line so that each of the divided interconnect lines  
            is coupled to each of said circuit elements, respectively.

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            7.     The method according to claim 3, further comprising:  
                    covering said shielding film with a protective film, said  
            protective film comprising a material having higher corrosion  
            resistance than that of a material which is included in said  
30    shielding film.

            8.     The method according to claim 4, further comprising:  
                    covering said shielding film with a protective film, said

protective film comprising a material having higher corrosion resistance than that of a material which is included in said shielding film.

- 5 9. The method according to claim 5, further comprising:  
covering said shielding film with a protective film, said  
protective film comprising a material having higher corrosion  
resistance than that of a material which is included in said  
shielding film.

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